

TECHNICAL DATA DATASHEET 5068, REV.A

# HERMETIC POWER SCHOTTKY RECTIFIER Low Reverse Leakage Low Forward Voltage Drop

# **Applications:**

- Switching Power Supply Converters Free-Wheeling Diodes Polarity Protection Diode •
- 60A 60V Schottky rectifier in SHD-3 package

#### Features:

- Low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

# **Maximum Ratings:**

ALL RATINGS ARE @  $T_C = 25$  °C UNLESS OTHERWISE SPECIFIED.

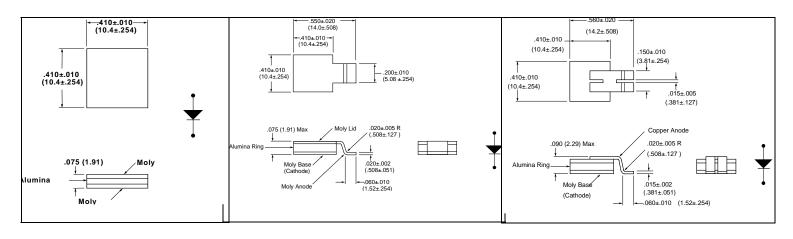
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	60	V
Max. Average Forward Current	I <sub>F(AV)</sub>	-	60	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine wave	600	Α
Max. Junction Temperature	$T_J$	-	-65 to +175	°C
Max. Storage Temperature	T <sub>stg</sub>	-	-65 to +175	°C
Max. Thermal Resistance	$R_{\theta JC}$	-	0.40	°C/W

#### **Electrical Characteristics:**

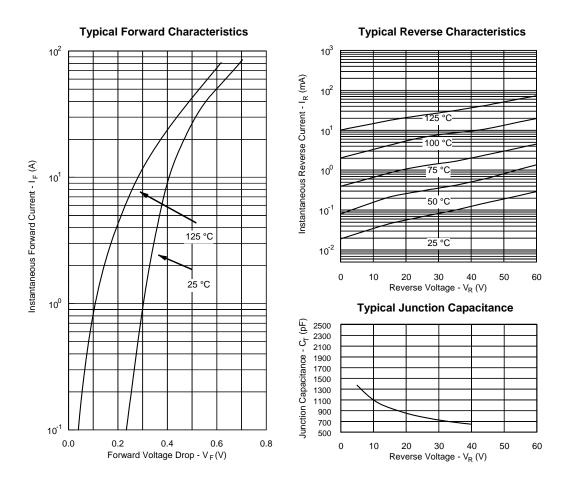
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 60A, Pulse, T <sub>J</sub> = 25 °C	0.78	V
	$V_{F2}$	@ 60A, Pulse, T <sub>J</sub> = 125 °C	0.71	V
Max. Reverse Current	I <sub>R1</sub>	@ $V_R = 60V$ , Pulse, $T_J = 25  ^{\circ}C$	1.2	mA
	I <sub>R2</sub>	@V <sub>R</sub> = 60V, Pulse, T <sub>J</sub> = 125 °C	90	mA
Max. Junction Capacitance	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C	2600	рF
		$f_{SIG} = 1MHz$ , $V_{SIG} = 50mV$ (p-p)		

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## Mechanical Dimensions: in inches / mm



SHD-3A SHD-3B





SHD114523 SHD114523A SHD114523B

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